

WHAT IS CLAIMED IS:

1. A semiconductor structure, comprising:
a semiconductor chip; and
a conductive layer disposed over a portion of the chip, the conductive layer having a portion that extends beyond an edge of the chip.
2. The structure of claim 1, wherein the conductive layer comprises a metal line.
3. The semiconductor structure of claim 1, wherein the chip comprises a device.
4. The semiconductor structure of claim 3, wherein the device comprises an integrated circuit.
5. The semiconductor structure of claim 3, wherein the device comprises a micro-electromechanical device.
6. The semiconductor structure of claim 3, further comprising:
a contact pad disposed on a surface of said device, wherein a portion of the conductive layer is in electrical communication with said contact pad.
7. The semiconductor structure of claim 1, further comprising:
a front layer, having a first portion disposed on a first surface of the semiconductor chip, and a second portion extending beyond the edge of the chip, the conductive layer being disposed on the front layer.
8. The semiconductor structure of claim 7, wherein the front layer is a dielectric layer.
9. The semiconductor structure of claim 7, wherein the front layer is compliant.
10. The semiconductor structure of claim 7, wherein the front layer includes a bump.

11. A semiconductor structure, comprising:
a semiconductor chip; and
a front layer, having a first portion disposed on a first surface of the semiconductor chip, and a second portion extending beyond an edge of the chip.
12. A method for making a semiconductor structure, comprising:
providing a semiconductor chip having a device formed thereon; and
forming a layer over a portion of the device, wherein a portion of the layer extends beyond an outer edge of the device.
13. The method of claim 12, wherein the layer is a conductive layer.
14. The method of claim 13, further comprising:
defining a line in the conductive layer.
15. The method of claim 13, further comprising:
forming a front layer having a first portion disposed on a first surface of the device, and a second portion extending beyond the edge of the device, the conductive layer being disposed on the front layer.
16. The method of claim 13, wherein the device is formed proximate a first surface of the chip, further comprising:
forming an encapsulating layer proximate a second surface of the chip,
wherein the portion of the front layer extending beyond the outer edge of the device extends over the encapsulating layer.
17. A method for making a semiconductor structure, comprising:
providing a plurality of semiconductor chips; and
forming a first encapsulating layer between each of the semiconductor chips, wherein the encapsulating layer bonds the chips together.

18. The method of claim 16, further comprising:
forming a second encapsulating layer over the backside of the chips.

10044000-103101